COMPLETE IF KNOWN 10/681,553 **Application Number** INFORMATION DISCLOSURE MINFORMATION DISCLOSURE
STATEMENT BY APPLICANT 7774 Confirmation Number Filing Date October 7, 2003 Form PTO-1449 (Modified) First Named Inventor Eric J. BERGMAN (Use several sheets if necessary) **Group Art Unit** 1746 **Examiner Name** Sheet of Attomey Docket No. 54008.8012.US04 (P96-0015US5)

				U.S. PATENT DOCUMENTS				
Examiner Initials*	Cite No.	U.S. Patent or Application Kind Code NUMBER (if known)		Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines Where Relevant Passage Relevant Figures Appe	es or	
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EM No. EV	254990096US			COMPLETE IF KNOWN			
				Application Number	Not yet assigned		
	INFORMATION			Confirmation Number			
•	-	BY APPLICANT		Filing Date	October 7, 2003		
		149 (Modified)		First Named Inventor	Eric J. BERGMAN		
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Sheet	1	of	5	Attorney Docket No.	54008.8012.US04		

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Attorney Docket No.

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	STATEMENT BY APPLICANT				October 7, 2003	
		149 (Modified)		First Named Inventor	Eric J. BERGMAN	
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Sheet	5	of	5	Attorney Docket No.	54008.8012.US04	

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				Filing Date	October 7, 2003	
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